METHODS OF FORMING LaNiO₃ CONDUCTIVE LAYERS, FERRO-ELECTRIC DEVICES WITH LaNiO₃ LAYERS, AND PRECURSOR FORMATION SOLUTIONS

ABSTRACT OF THE DISCLOSURE

Methods of forming lanthanum nickel oxide (LaNiO₃) layers with precursor formation solutions are disclosed, along with devices made from such solutions. Also disclosed are methods for making the formation solutions using lanthanum, nickel, and a diol. The present invention enables the manufacture of LaNiO₃ layers at low cost, with good resistivity properties, and a surface morphology suitable for interfacing to a ferroelectric material.